

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	200	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	200	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	5	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	4.5	A
Peak Pulse Current	I _{CM}	6	A
Base Current	I _B	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

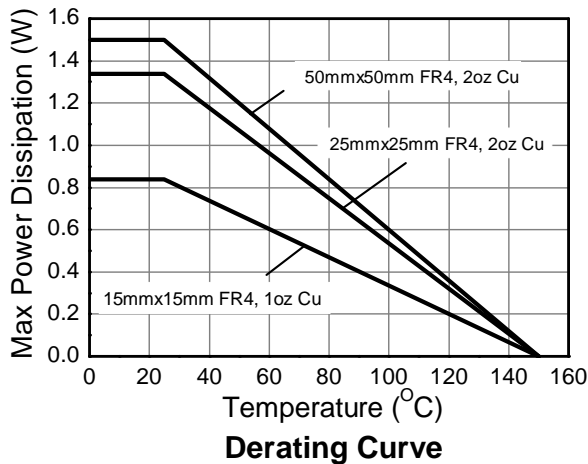
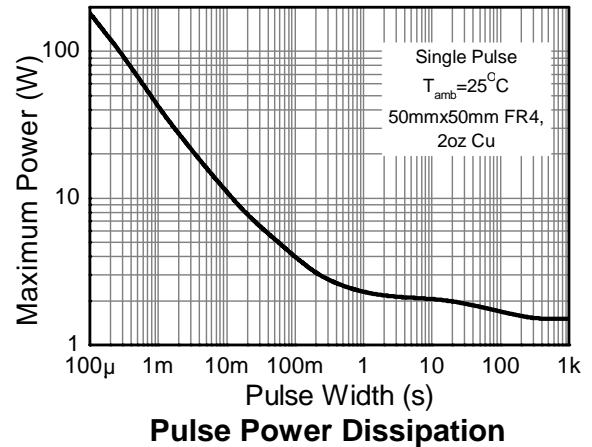
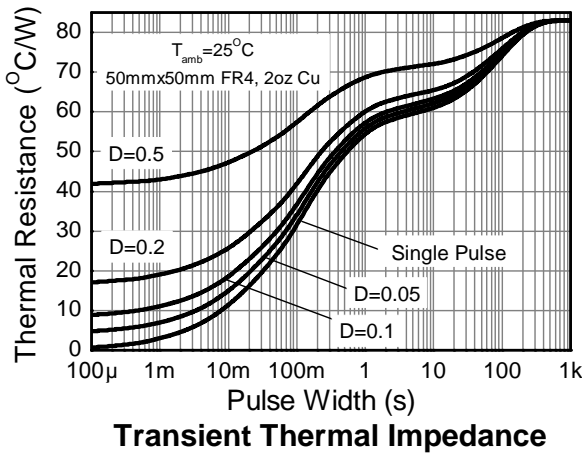
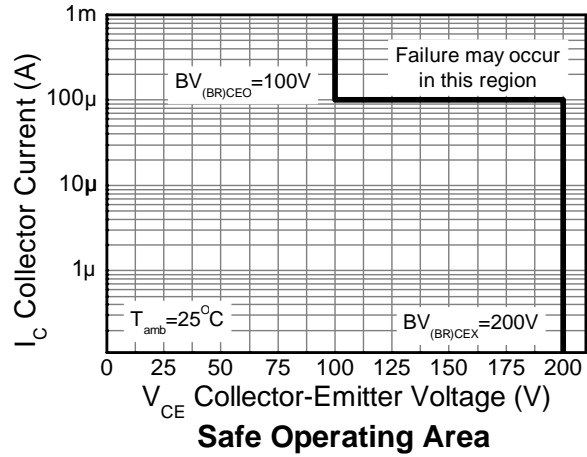
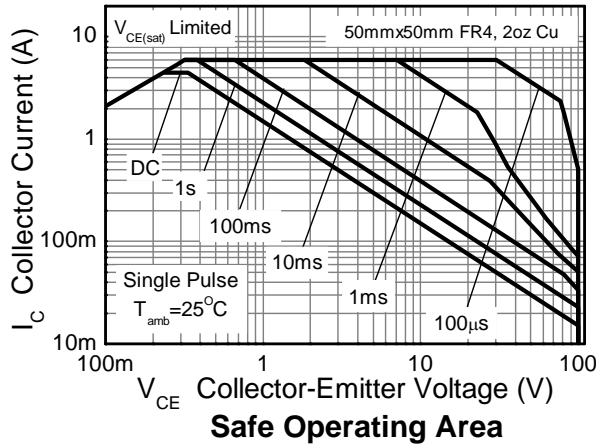
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	0.84	W mW/°C
		6.72	
		1.34	
		10.72	
		1.50	
Thermal Resistance, Junction to Ambient	R _{θJA}	12.0	°C/W
		2.0	
		16.0	
		149	
Thermal Resistance, Junction to Ambient	R _{θJA}	93	°C/W
		83	
		60	
Thermal Resistance, Junction to Lead	R _{θJL}	43.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 - Same as Note 7, whilst measured at t < 5 seconds.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

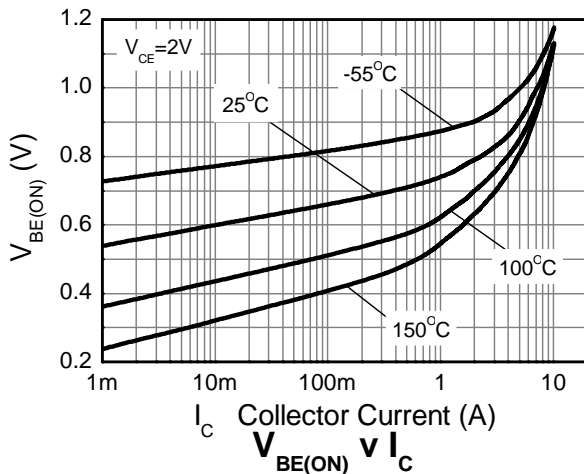
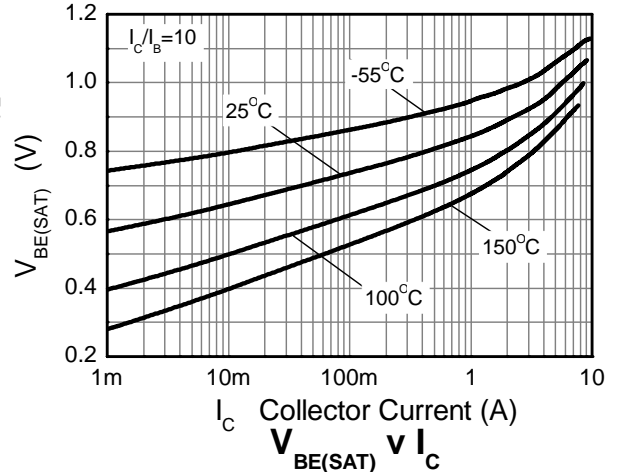
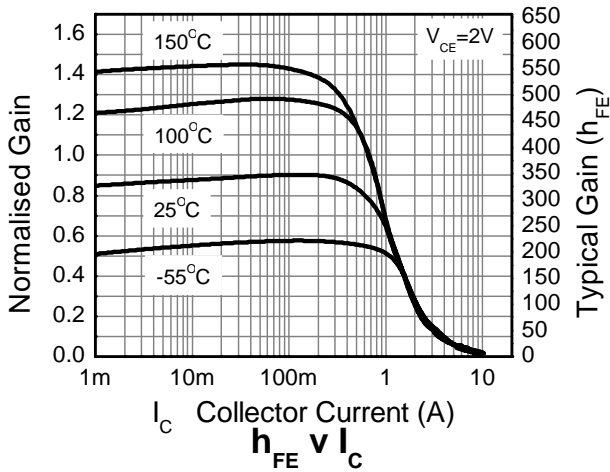
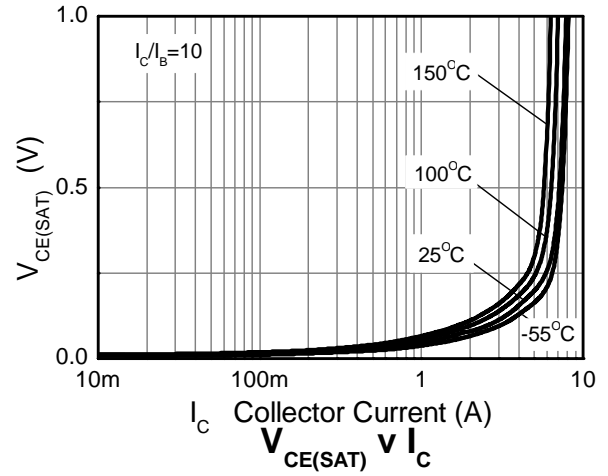
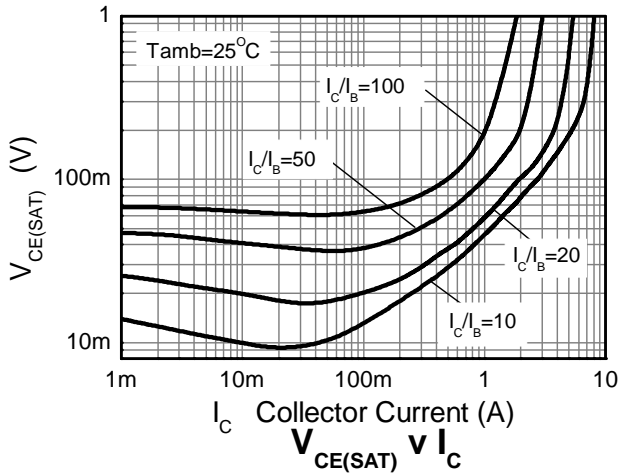


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	200	240	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Forward Blocking)	BV _{CEX}	200	240	—	V	I _C = 100μA, R _{BE} < 1kΩ or -1V < V _{BE} < 0.25V
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	100	120	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	—	V	I _E = 100μA
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	6	8.3	—	V	I _E = 100μA, R _{BC} < 1kΩ or 0.25V < V _{BC} < -0.25V
Emitter-Collector Breakdown Voltage (Base Open)	BV _{ECO}	5	8	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	<1	50	nA μA	V _{CB} = 160V V _{CB} = 160V, T _A = +100°C
Emitter-Base Cutoff Current	I _{EBO}	—	<1	50	nA	V _{EB} = 5.6V
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h _{FE}	200 130 —	350 250 25	500 — —	—	I _C = 100mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 5A, V _{CE} = 2V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	45 105 170	60 135 235	mV	I _C = 1A, I _B = 100mA I _C = 1A, I _B = 20mA I _C = 4.5A, I _B = 450mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	950	1050	mV	I _C = 4.5A, I _B = 450mA
Base-Emitter On Voltage	V _{BE(ON)}	—	880	1000	mV	I _C = 4.5A, V _{CE} = 2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	—	150	—	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz
Input Capacitance	C _{I BO}	—	305	—	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{O BO}	—	15.7	25	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _D	—	28.3	—	ns	V _{CC} = 10V, I _C = 500mA, I _{B1} = I _{B2} = 50mA
Rise Time	t _R	—	23.6	—	ns	
Storage Time	t _S	—	962	—	ns	
Fall Time	t _F	—	133	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

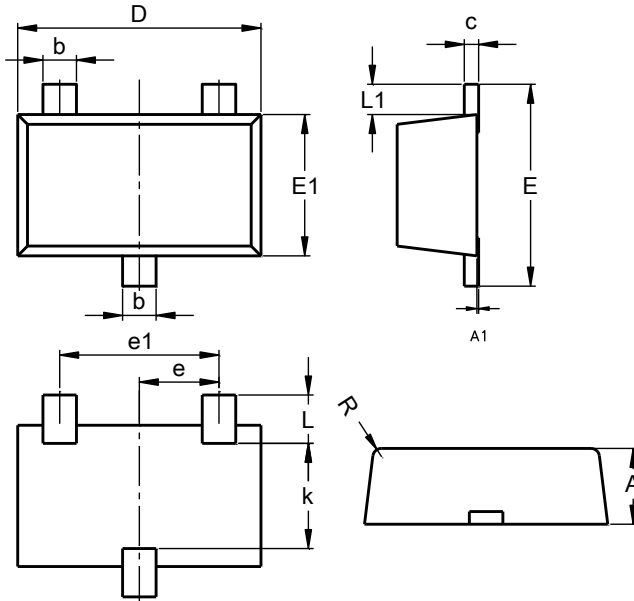
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23F

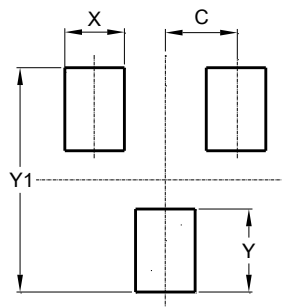


SOT23F			
Dim	Min	Max	Typ
A	0.80	1.00	0.90
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	0.190 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23F



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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